

L Number	Hits	Search Text	DB	Time stamp
1	7243	((electron adj beam) and primary and semiconductor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 15:56
2	628	((electron adj beam) and primary and semiconductor) and (circuit adj board)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 15:47
3	0	(((electron adj beam) and primary and semiconductor) and (circuit adj board)) and (shrinkage near4 board)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 15:48
4	1	(((electron adj beam) and primary and semiconductor) and (circuit adj board)) and (shrinkage near4 (board or pattern or circuit))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 15:57
5	333	(electron adj beam) and (primary adj beam) and semiconductor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 15:56
6	0	((electron adj beam) and (primary adj beam) and semiconductor) and (shrinkage near4 (board or pattern or circuit))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 15:57

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4	1	(((electron adj beam) and primary and semiconductor) and (circuit adj board)) and (shrinkage near4 (board or pattern or circuit))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 15:59
5	333	(electron adj beam) and (primary adj beam) and semiconductor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 15:56
6	0	((electron adj beam) and (primary adj beam) and semiconductor) and (shrinkage near4 (board or pattern or circuit))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 15:57
7	2	(((electron adj beam) and primary and semiconductor) and (circuit adj board)) and ((shrinkage or worp\$3) near5 (board or pattern or circuit))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/10/06 16:01

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1	7243	((electron adj beam) and primary and semiconductor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT;	2004/10/06 15:56
2	628	((electron adj beam) and primary and semiconductor) and (circuit adj board)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT;	2004/10/06 15:47
3	0	(((electron adj beam) and primary and semiconductor) and (circuit adj board)) and (shrinkage near4 board)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT;	2004/10/06 15:48
4	1	(((electron adj beam) and primary and semiconductor) and (circuit adj board)) and (shrinkage near4 (board or pattern or circuit))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT;	2004/10/06 15:59
5	333	(electron adj beam) and (primary adj beam) and semiconductor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT;	2004/10/06 15:56
6	0	((electron adj beam) and (primary adj beam) and semiconductor) and (shrinkage near4 (board or pattern or circuit))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT;	2004/10/06 15:57
7	2	(((electron adj beam) and primary and semiconductor) and (circuit adj board)) and ((shrinkage or worp\$3) near5 (board or pattern or circuit))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB USPAT;	2004/10/06 16:01